8. The method for producing a hybrid substrate of any one of claims 1 to 7 wherein the terrace portion has a width of 1 mm to 3 mm.

9. The method for producing a hybrid substrate of any one of claims 1 to 8 wherein the silicon active layer in the SOI substrate is free of vacancy defects and suffers no oxidation-induced stacking faults upon thermal oxidation.

10. The method for producing a hybrid substrate of any one of claims 1 to 9, further comprising the step of subjecting the support substrate to heat treatment in a reducing atmosphere, prior to the step of bonding the SOI substrate to the support substrate.

11. The method for producing a hybrid substrate of any one of claims 1 to 10 wherein the support substrate is thinned such that the surface of the support substrate to be bonded to the SOI substrate includes an outer peripheral region of predetermined width which is depressed relative to a central portion.